



H2N6718L

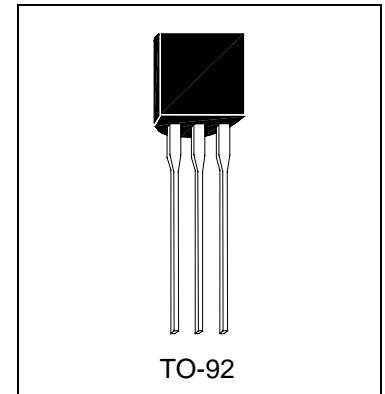
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The H2N6718L is designed for general purpose medium power amplifier and switching applications.

Features

- High Power: 850mW
- High Current: 1A



Absolute Maximum Ratings

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (Ta=25°C) 850 mW
- Maximum Voltages and Currents (Ta=25°C)
 - VCBO Collector to Base Voltage 100 V
 - VCEO Collector to Emitter Voltage 100 V
 - VEBO Emitter to Base Voltage 5 V
 - IC Collector Current (Continue) 1 A
 - IC Collector Current (Pulse) 2 A
 - IB Base Current (Continue) 200 mA

Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=100uA
BVCEO	100	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=80V
*VCE(sat)	-	-	350	mV	IB=35mA, IC=350mA
*hFE1	80	-	-		VCE=1V, IC=50mA
*hFE2	50	-	300		VCE=1V, IC=250mA
*hFE3	20	-	-		VCE=1V, IC=500mA
fT	50	-	-	MHz	VCE=10V, IC=50mA, f=100MHz
Cob	-	-	20	pF	VCB=10V, IE=0, f=1MHz

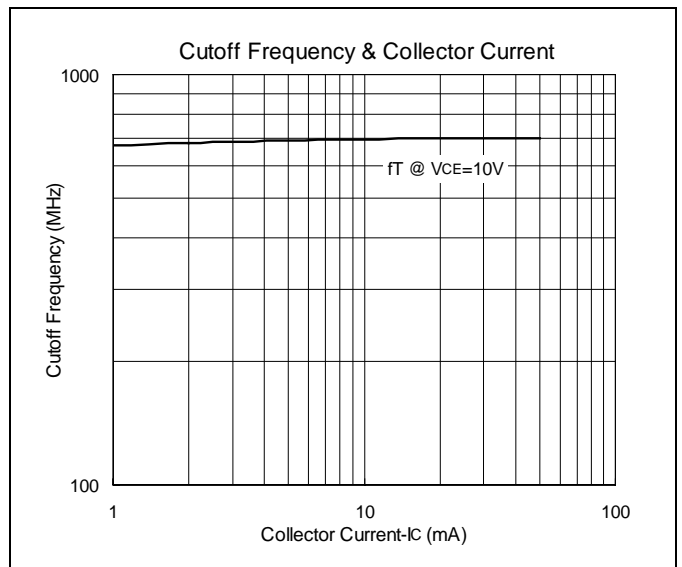
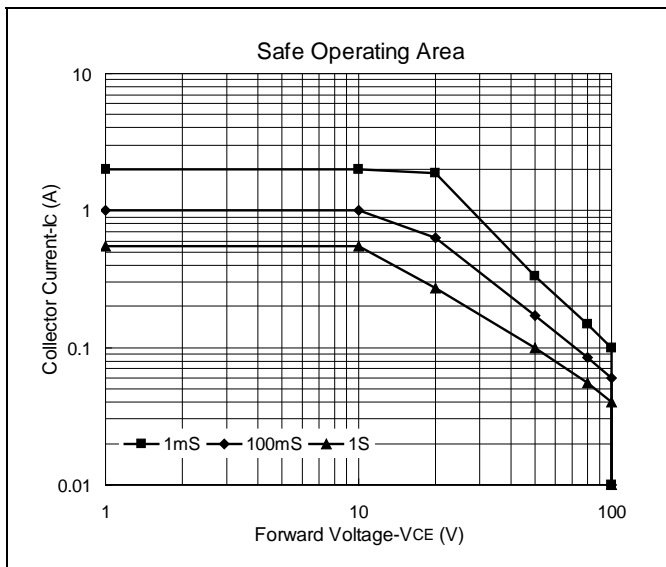
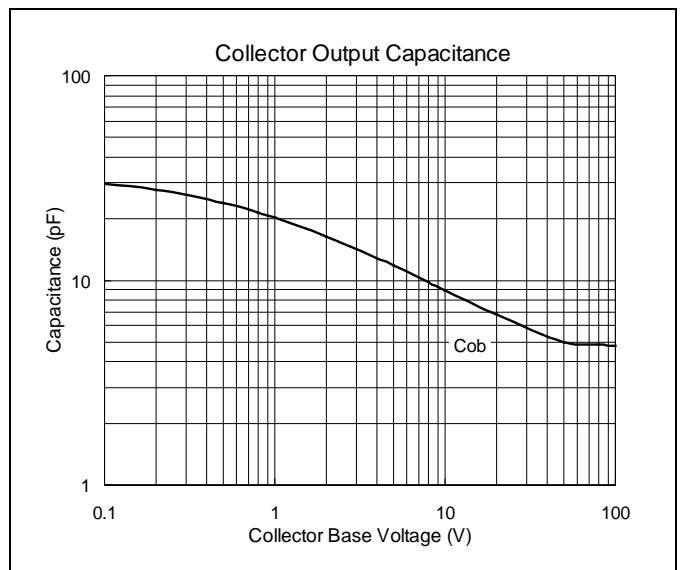
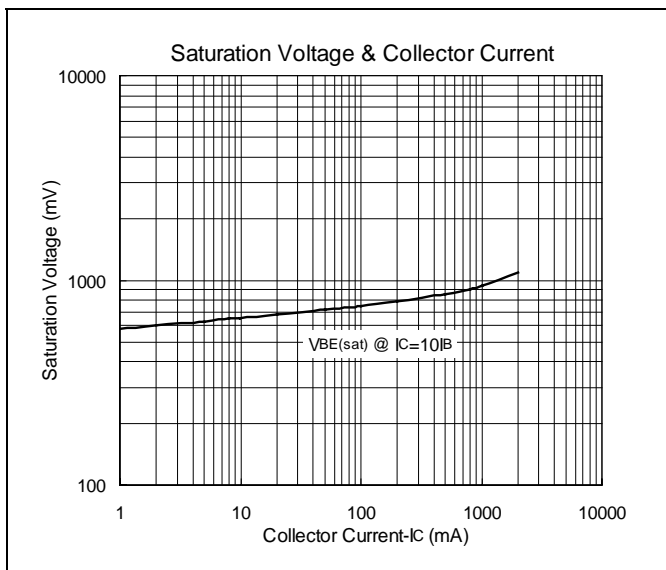
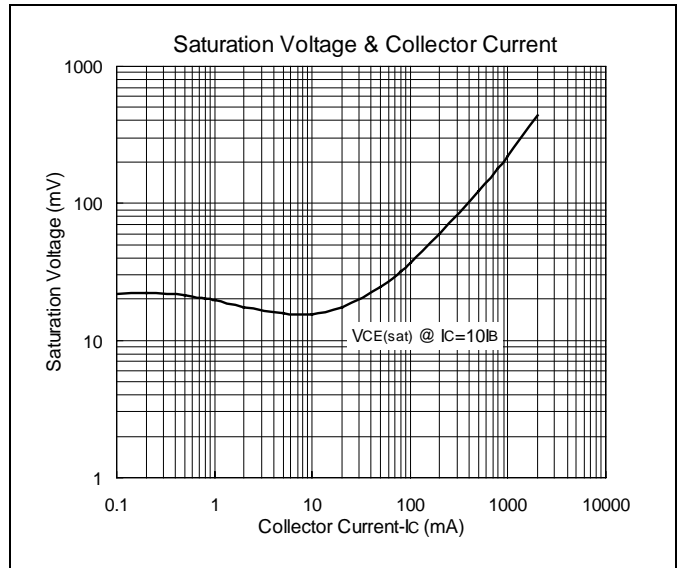
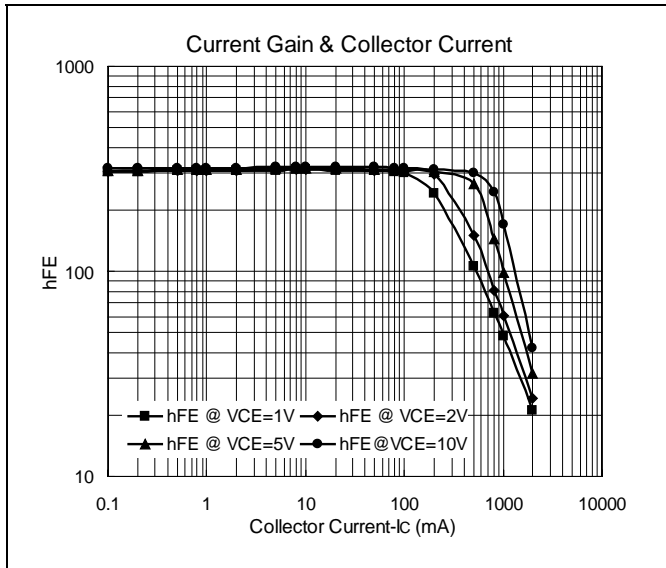
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

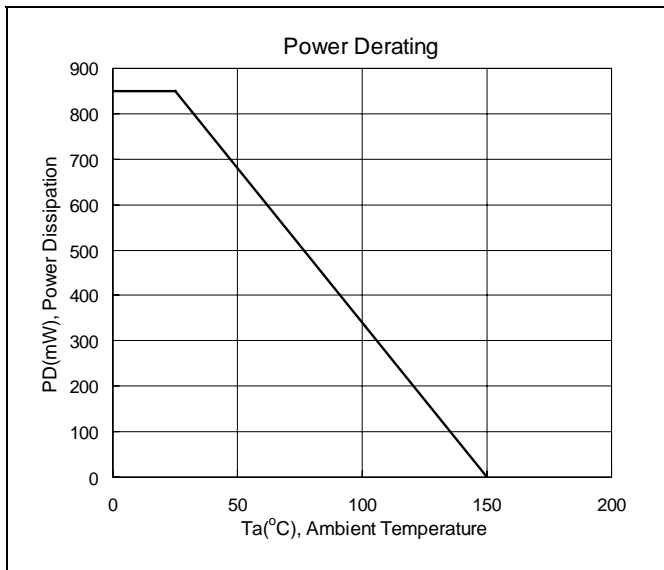
Classification Of hFE2

Rank	A	B
Range	50-115	95-300



Characteristics Curve







TO-92 Dimension

3-Lead TO-92 Plastic Package
HSMC Package Code: A

Marking:

Pb Free Mark
 Pb-Free: " * " (Note)
 Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1. Emitter 2. Collector 3. Base

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

*: Typical, Unit: mm

TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1,F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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Head Office And Factory:

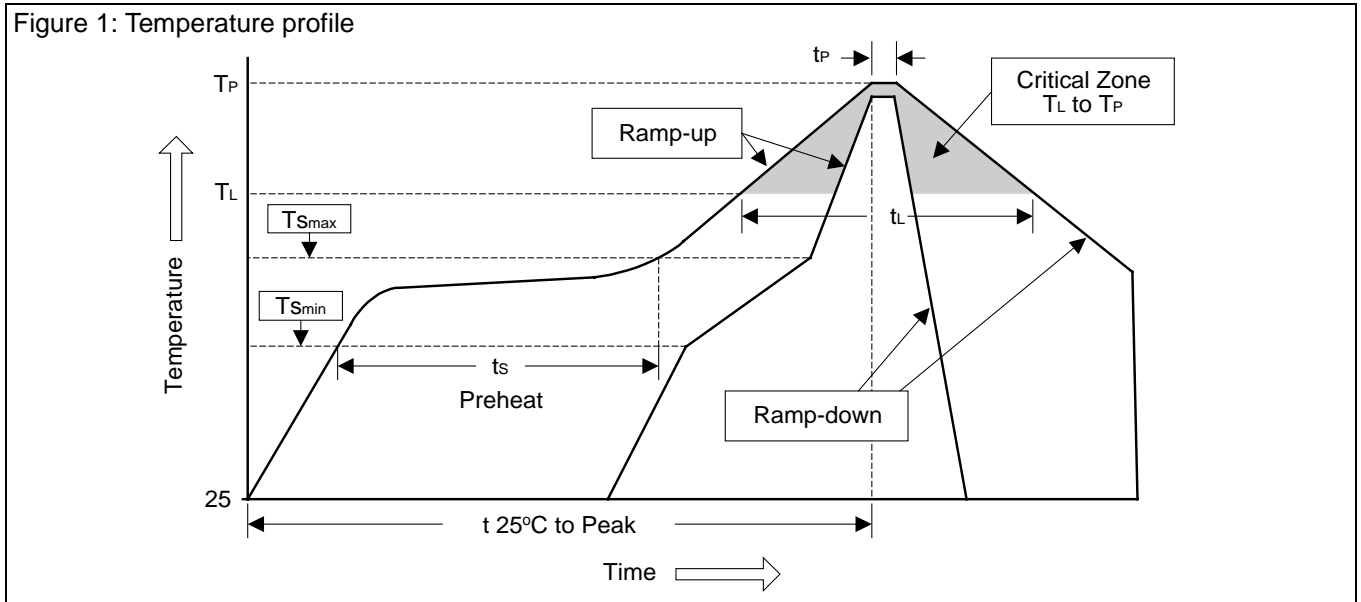
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ($T_{s_{min}}$)	100°C	150°C
- Temperature Max ($T_{s_{max}}$)	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
$T_{s_{max}}$ to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec